

Jinn-Kong Sheu

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

285
papers

6,194
citations

41
h-index

65
g-index

321
ext. papers

6,646
ext. citations

3.2
avg, IF

5.26
L-index

#	Paper	IF	Citations
285	High-Responsivity Solar-Blind Photodetectors Formed by Ga ₂ O ₃ /p-GaN Bipolar Heterojunctions. <i>ACS Photonics</i> , 2022 , 9, 1002-1007	6.3	2
284	Improved Performance of GaN Photoelectrodes from the Facile Fabrication of a Binder-Free Catalyst: Ni(OH) ₂ Nanosheets. <i>ACS Applied Energy Materials</i> , 2022 , 5, 3471-3476	6.1	1
283	AlGa _N -Based Deep Ultraviolet Light-Emitting Diodes with Thermally Oxidized Al Ga O Sidewalls.. <i>ACS Omega</i> , 2022 , 7, 15027-15036	3.9	0
282	Stable Photoelectrochemical Water Splitting Using p _n GaN Junction Decorated with Nickel Oxides as Photoanodes. <i>Journal of Physical Chemistry C</i> , 2021 , 125, 16776-16783	3.8	2
281	Effect of KOH-Treatment at Sol-Gel Derived NiO _x Film on GaN Photoanodes in Hydrogen Generation. <i>ACS Applied Energy Materials</i> , 2021 , 4, 8030-8035	6.1	
280	Achievement of 110-nm-Wide Spectral Width in Monolithic Tunnel-Junction Light-Emitting Diode. <i>IEEE Journal of Quantum Electronics</i> , 2021 , 57, 1-6	2	
279	Scalable and sustainable synthetic assessment between solid-state metathesis and sonochemically derived electrocatalysts (strontium molybdate) for the precise anti-androgen bicalutamide (Casodex) detection. <i>Microchemical Journal</i> , 2021 , 168, 106465	4.8	1
278	Deep Ultraviolet AlGa _N -Based Light-Emitting Diodes with p-AlGa _N /AlGa _N Superlattice Hole Injection Structures. <i>Processes</i> , 2021 , 9, 1727	2.9	1
277	Terahertz Photoacoustic Generation Using Ultrathin Nickel Nanofilms. <i>Journal of Physical Chemistry C</i> , 2021 , 125, 3134-3142	3.8	5
276	Observation of Femtosecond Acoustic Anomaly in a Solid Liquid Interface. <i>Journal of Physical Chemistry C</i> , 2020 , 124, 2987-2993	3.8	2
275	High-power and single-mode VCSEL arrays with single-polarized outputs by using package-induced tensile strain. <i>Optics Letters</i> , 2020 , 45, 4839-4842	3	9
274	UV light-emitting diodes grown on GaN templates with selective-area Si implantation. <i>Optics Express</i> , 2020 , 28, 4674-4685	3.3	2
273	Ultra-short photoacoustic pulse generation through hot electron pressure in two-dimensional electron gas. <i>Optics Express</i> , 2020 , 28, 34045-34053	3.3	
272	AlGa _N -based deep ultraviolet light emitting diodes with magnesium delta-doped AlGa _N last barrier. <i>Applied Physics Letters</i> , 2020 , 117, 251101	3.4	7
271	Suppressing the Initial Growth of Sidewall GaN by Modifying AlN-Coated Patterned Sapphire with KOH-Based Etchant. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 016012	2	
270	Studying time-dependent contribution of hot-electron versus lattice-induced thermal-expansion response in ultra-thin Au-nanofilms. <i>Applied Physics Letters</i> , 2020 , 117, 154101	3.4	3
269	Al _{0.3} Ga _{0.7} N/GaN heterostructure transistors with a regrown p-GaN gate formed with selective-area Si implantation as the regrowth mask. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2020 , 124, 114367	3	2

268	Rationally designed RGO@CuO@Mn ₂ O ₃ as an excellent electrocatalyst for the rapid and real-time detection of 2-nitrophenol. <i>New Journal of Chemistry</i> , 2020 , 44, 12465-12472	3.6	10
267	Cobalt Oxide Nanofilms on n-GaN Working Electrodes for Photoelectrochemical Water Splitting. <i>Journal of Physical Chemistry C</i> , 2020 , 124, 25196-25201	3.8	
266	NiOx nanoparticles as active water splitting catalysts for the improved photostability of a n-GaN photoanode. <i>Solar Energy Materials and Solar Cells</i> , 2020 , 216, 110723	6.4	4
265	Photoelectrochemical Generation of Hydrogen and Formic Acid Using GaN Films Decorated with TiO ₂ /Ag Nanoparticles Composite Structure as Photoelectrodes. <i>Journal of Physical Chemistry C</i> , 2020 , 124, 9591-9598	3.8	7
264	Graphene Quantum Dot Vertical Cavity Surface-Emitting Lasers. <i>ACS Photonics</i> , 2019 , 6, 2894-2901	6.3	5
263	A curvature-tunable random laser. <i>Nanoscale</i> , 2019 , 11, 3534-3545	7.7	28
262	. <i>Journal of Lightwave Technology</i> , 2019 , 37, 1225-1230	4	1
261	Verification of complex acoustic mismatch model in sub-THz regime. <i>Applied Physics Letters</i> , 2019 , 114, 151106	3.4	3
260	Light-emitting diodes with surface gallium nitride p-n homojunction structure formed by selective area regrowth. <i>Scientific Reports</i> , 2019 , 9, 3243	4.9	10
259	Enhanced production rates of hydrogen generation and carbon dioxide reduction using aluminum gallium nitride/gallium nitride heteroepitaxial films as photoelectrodes in seawater. <i>Solar Energy Materials and Solar Cells</i> , 2019 , 202, 110153	6.4	5
258	Mn valence state mediated room temperature ferromagnetism in nonpolar Mn doped GaN. <i>Applied Surface Science</i> , 2019 , 473, 693-698	6.7	14
257	Design of GaN-Based Multicolor Tunnel-Junction Light-Emitting Diodes. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 165-171	2.9	4
256	GaN intermediate band solar cells with Mn-doped absorption layer. <i>Scientific Reports</i> , 2018 , 8, 8641	4.9	9
255	Suppressing the Initial Growth of Sidewall GaN by Modifying Micron-Sized Patterned Sapphire Substrate with H ₂ O ₂ -Based Etchant. <i>Micromachines</i> , 2018 , 9,	3.3	2
254	GaN-Based Cyan Light-Emitting Diode with up to 1-GHz Bandwidth for High-Speed Transmission Over SI-POF. <i>IEEE Photonics Journal</i> , 2017 , 9, 1-7	1.8	9
253	InGaN-based epitaxial films as photoelectrodes for hydrogen generation through water photoelectrolysis and CO ₂ reduction to formic acid. <i>Solar Energy Materials and Solar Cells</i> , 2017 , 166, 86-90	6.4	26
252	Photoelectrochemical hydrogen generation from water using undoped GaN with selective-area Si-implanted stripes as a photoelectrode. <i>Journal of Materials Chemistry A</i> , 2017 , 5, 22625-22630	13	6
251	In Situ Monitoring of Chemical Reactions at a Solid-Water Interface by Femtosecond Acoustics. <i>Journal of Physical Chemistry Letters</i> , 2017 , 8, 5430-5437	6.4	10

250	Carrier dynamics of Mn-induced states in GaN thin films. <i>Scientific Reports</i> , 2017 , 7, 5788	4.9	8
249	Theoretical Investigation of Efficient Green Tunnel-Junction Light-Emitting Diodes. <i>IEEE Electron Device Letters</i> , 2017 , 38, 75-78	4.4	3
248	Extracting elastic properties of an atomically thin interfacial layer by time-domain analysis of femtosecond acoustics. <i>Applied Physics Letters</i> , 2017 , 111, 213101	3.4	5
247	Planar GaN-Based Blue Light-Emitting Diodes With Surface p-n Junction Formed by Selective-Area SiIbn Implantation. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 4156-4160	2.9	8
246	Monolithic stacked blue light-emitting diodes with polarization-enhanced tunnel junctions. <i>Optics Express</i> , 2017 , 25, A777-A784	3.3	6
245	III \bar{V} Nitride-Based Photodetection. <i>Series in Optics and Optoelectronics</i> , 2017 , 597-613		
244	Manganese-doped AlGa \bar{N} /GaN heterojunction solar cells with intermediate band absorption. <i>Solar Energy Materials and Solar Cells</i> , 2016 , 157, 727-732	6.4	11
243	THz Acoustic Spectroscopy by using Double Quantum Wells and Ultrafast Optical Spectroscopy. <i>Scientific Reports</i> , 2016 , 6, 28577	4.9	7
242	Physical properties of Al-doped MgZnO/AlGa \bar{N} p \bar{n} heterojunction photodetectors. <i>Optical and Quantum Electronics</i> , 2016 , 48, 1	2.4	1
241	III-Nitride-Based Cyan Light-Emitting Diodes With GHz Bandwidth for High-Speed Visible Light Communication. <i>IEEE Electron Device Letters</i> , 2016 , 1-1	4.4	25
240	Enhancing UV-emissions through optical and electronic dual-function tuning of Ag nanoparticles hybridized with n-ZnO nanorods/p-GaN heterojunction light-emitting diodes. <i>Nanoscale</i> , 2016 , 8, 4463-747	7.7	26
239	GaN-Based UV Light-Emitting Diodes With a Green Indicator Through Selective-Area Photon Recycling. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 1122-1127	2.9	2
238	Mask-free regrowth of GaN p-i-n structure on selective-area Si-implanted n-GaN template layer. <i>Acta Materialia</i> , 2016 , 108, 17-25	8.4	4
237	Design of Hole-Blocking and Electron-Blocking Layers in Al \bar{x} Ga $\bar{1-x}$ N-Based UV Light-Emitting Diodes. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 1141-1147	2.9	21
236	GaN based Cyan light-emitting diodes with GHz bandwidth 2016 ,		3
235	Warm-white light-emitting diode with high color rendering index fabricated by combining trichromatic InGa \bar{N} emitter with single red phosphor. <i>Optics Express</i> , 2015 , 23, A232-9	3.3	14
234	GaN-based photon-recycling green light-emitting diodes with vertical-conduction structure. <i>Optics Express</i> , 2015 , 23, A371-81	3.3	4
233	White emission from non-planar InGa \bar{N} /GaN MQW LEDs grown on GaN template with truncated hexagonal pyramids. <i>Optics Express</i> , 2015 , 23, A401-12	3.3	19

232	Effects of Temperature on Niobium-Doped MgZnO Films Grown Using Radio-Frequency Magnetron Sputtering. <i>ECS Journal of Solid State Science and Technology</i> , 2015 , 4, Q96-Q100	2	
231	. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 2919-2923	2.9	5
230	THz acoustic phonon spectroscopy and nanoscopy by using piezoelectric semiconductor heterostructures. <i>Ultrasonics</i> , 2015 , 56, 52-65	3.5	36
229	Probing hydrophilic interface of solid/liquid-water by nanoultrasonics. <i>Scientific Reports</i> , 2014 , 4, 6249	4.9	36
228	Surface Plasmon-Enhanced GaN Metal/Insulator/Semiconductor Ultraviolet Detectors With Ag Nanoislands Embedded in a Silicon Dioxide Gate Layer. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2014 , 20, 137-141	3.8	5
227	Selective Growth of AlGaIn-Based p-i-n UV Photodiodes Structures. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2014 , 20, 173-177	3.8	0
226	Ultraviolet/blue light-emitting diodes based on single horizontal ZnO microrod/GaN heterojunction. <i>Nanoscale Research Letters</i> , 2014 , 9, 446	5	18
225	Ga ₂ O ₃ Films for Photoelectrochemical Hydrogen Generation. <i>Journal of the Electrochemical Society</i> , 2014 , 161, H508-H511	3.9	20
224	Passively gain-switched and self mode-locked thulium fiber laser at 1950 nm. <i>Optics and Laser Technology</i> , 2014 , 56, 354-357	4.2	17
223	Determination of s-d exchange coupling in GaMnN by time-resolved Kerr rotation spectroscopy. <i>Physical Review B</i> , 2014 , 90,	3.3	2
222	Photoelectrochemical hydrogen generation with linear gradient Al composition dodecagon faceted AlGaIn/n-GaN electrode. <i>Optics Express</i> , 2014 , 22 Suppl 7, A1853-61	3.3	4
221	Slanted n-ZnO/p-GaN nanorod arrays light-emitting diodes grown by oblique-angle deposition. <i>APL Materials</i> , 2014 , 2, 056101	5.7	24
220	Vertical InGaIn-based green-band solar cells operating under high solar concentration up to 300 suns. <i>Optics Express</i> , 2014 , 22 Suppl 5, A1222-8	3.3	15
219	Thermal stability of post-growth-annealed Ga-doped MgZnO films grown by the RF sputtering method. <i>Materials Research Society Symposia Proceedings</i> , 2014 , 1675, 41-44		
218	Temperature-Dependent Current-Voltage Characteristics of Al-Doped Mg _x Zn _{1-x} O/AlGaIn-p Junction Diodes. <i>ECS Journal of Solid State Science and Technology</i> , 2014 , 3, Q65-Q68	2.8	7
217	GaN-Based Dual-Color LEDs With p-Type Insertion Layer for Controlling the Ratio of Two-Color Intensities. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 2821-2826	2.9	6
216	Improving efficiency of InGaIn/GaN multiple quantum well solar cells using CdS quantum dots and distributed Bragg reflectors. <i>Solar Energy Materials and Solar Cells</i> , 2013 , 117, 531-536	6.4	23
215	Efficient collection of photogenerated carriers by inserting double tunnel junctions in III-nitride p-i-n solar cells. <i>Applied Physics Letters</i> , 2013 , 103, 193503	3.4	8

214	Improved Output Power of GaN-based Blue LEDs by Forming Air Voids on Ar-Implanted Sapphire Substrate. <i>Journal of Lightwave Technology</i> , 2013 , 31, 1318-1322	4	14
213	GaN-Based Planar p-i-n Photodetectors With the Be-Implanted Isolation Ring. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 1178-1182	2.9	13
212	Photoresponses of manganese-doped gallium nitride grown by metalorganic vapor-phase epitaxy. <i>Applied Physics Letters</i> , 2013 , 102, 071107	3.4	7
211	Enhanced AlGaIn/GaN MOS-HEMT Performance by Using Hydrogen Peroxide Oxidation Technique. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 213-220	2.9	55
210	Dual-wavelength GaN-based LEDs grown on truncated hexagonal pyramids formed by selective-area regrowth on Si-implanted GaN templates. <i>Optics Express</i> , 2013 , 21 Suppl 5, A864-71	3.3	7
209	Numerical study of the suppressed efficiency droop in blue InGaIn LEDs with polarization-matched configuration. <i>Optics Letters</i> , 2013 , 38, 3158-61	3	10
208	InGaIn working electrodes with assisted bias generated from GaAs solar cells for efficient water splitting. <i>Optics Express</i> , 2013 , 21 Suppl 6, A991-6	3.3	11
207	Acoustic spectroscopy for studies of vitreous silica up to 740 GHz. <i>AIP Advances</i> , 2013 , 3, 072126	1.5	6
206	Improved conversion efficiency of GaN-based solar cells with Mn-doped absorption layer. <i>Applied Physics Letters</i> , 2013 , 103, 063906	3.4	15
205	Thermal Boundary Resistance between GaN and Cubic Ice and THz Acoustic Attenuation Spectrum of Cubic Ice from Complex Acoustic Impedance Measurements. <i>Physical Review Letters</i> , 2013 , 111, 225901 ⁴	7.4	15
204	InGaIn Flip-Chip Light-Emitting Diodes With Embedded Air Voids as Light-Scattering Layer. <i>IEEE Electron Device Letters</i> , 2013 , 34, 1542-1544	4.4	8
203	GaN-Based Dual Color LEDs with P-Type Insertion Layer for Balancing Two-Color Intensities 2013 ,		1
202	Vertical InGaIn light-emitting diodes with Ag paste as bonding layer. <i>Microelectronics Reliability</i> , 2012 , 52, 949-951	1.2	3
201	Improved Output Power of InGaIn LEDs by Lateral Overgrowth on Si-Implanted n-GaN Surface to Form Air Gaps. <i>IEEE Journal of Quantum Electronics</i> , 2012 , 48, 1004-1009	2	6
200	Light Extraction Enhancement of GaN-Based Light-Emitting Diodes Using Crown-Shaped Patterned Sapphire Substrates. <i>IEEE Photonics Technology Letters</i> , 2012 , 24, 1212-1214	2.2	6
199	Non-alloyed Cr/Au Ohmic contacts to N-face and Ga-face n-GaN. <i>Journal of Alloys and Compounds</i> , 2012 , 516, 38-40	5.7	7
198	Laser-induced periodic structures for light extraction efficiency enhancement of GaN-based light emitting diodes. <i>Optics Express</i> , 2012 , 20, 5689-95	3.3	35
197	Gallium nitride-based light-emitting diodes with embedded air voids grown on Ar-implanted AlN/sapphire substrate. <i>Applied Physics Letters</i> , 2012 , 101, 151103	3.4	10

196	High-temperature stability of postgrowth-annealed Al-doped Mg _x Zn _{1-x} O films without the phase separation effect. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2012 , 30, 061201	1.3	4
195	Modulation Effects of Periodic Potentials on the Electronic Properties of Bilayer Bernal Graphene: Tight-Binding Model. <i>Journal of the Physical Society of Japan</i> , 2012 , 81, 014705	1.5	2
194	Vertical InGaN light-emitting diodes with a sapphire-face-up structure. <i>Optics Express</i> , 2012 , 20, A119-24	3.3	8
193	Immersed finger-type indium tin oxide ohmic contacts on p-GaN photoelectrodes for photoelectrochemical hydrogen generation. <i>Optics Express</i> , 2012 , 20 Suppl 2, A190-6	3.3	9
192	Femtosecond excitation of radial breathing mode in 2-D arrayed GaN nanorods. <i>Optics Express</i> , 2012 , 20, 16611	3.3	12
191	Sputtered ZnO-SiO ₂ nanocomposite light-emitting diodes with flat-top nanosecond laser treatment. <i>Optics Express</i> , 2012 , 20, 19635-42	3.3	4
190	Vertical InGaN light-emitting diode with a retained patterned sapphire layer. <i>Optics Express</i> , 2012 , 20 Suppl 6, A1019-25	3.3	5
189	Optical properties of Mn in regrown GaN-based epitaxial layers. <i>Optical Materials Express</i> , 2012 , 2, 469	2.6	4
188	Mn-doped GaN as photoelectrodes for the photoelectrolysis of water under visible light. <i>Optics Express</i> , 2012 , 20 Suppl 5, A678-83	3.3	13
187	GaN-Based Miniaturized Cyan Light-Emitting Diodes on a Patterned Sapphire Substrate With Improved Fiber Coupling for Very High-Speed Plastic Optical Fiber Communication. <i>IEEE Photonics Journal</i> , 2012 , 4, 1520-1529	1.8	33
186	GaN-based light emitting diodes with micro- and nano-patterned structures by femtosecond laser nonlinear decomposition. <i>Applied Physics Letters</i> , 2012 , 101, 131103	3.4	13
185	Carrier Dynamics in High-Efficiency Blue GaN Light-Emitting Diodes Under Different Bias Currents and Temperatures. <i>IEEE Photonics Journal</i> , 2012 , 4, 1870-1880	1.8	2
184	Confined acoustic vibrations in piezoelectric GaN nanorods 2012 ,		2
183	Effect of Growth Pressure of Undoped GaN Layer on the ESD Characteristics of GaN-Based LEDs Grown on Patterned Sapphire. <i>IEEE Photonics Technology Letters</i> , 2011 , 23, 968-970	2.2	11
182	Characteristics of InGaN/sapphire-based photovoltaic devices with different superlattice absorption layers and buffer layers 2011 ,		1
181	Characteristics of InGaN-based concentrator solar cells operating under 150X solar concentration. <i>Optics Express</i> , 2011 , 19 Suppl 4, A695-700	3.3	14
180	Hydrogen gas generation using n-GaN photoelectrodes with immersed Indium Tin Oxide ohmic contacts. <i>Optics Express</i> , 2011 , 19 Suppl 6, A1196-201	3.3	12
179	Linear photon up-conversion of 450 meV in InGaN/GaN multiple quantum wells via Mn-doped GaN intermediate band photodetection. <i>Optics Express</i> , 2011 , 19 Suppl 6, A1211-8	3.3	9

178	Electroluminescence of ZnO nanocrystal in sputtered ZnO-SiO ₂ nanocomposite light-emitting devices. <i>Optics Express</i> , 2011 , 19, 11873-9	3.3	9
177	High-performance GaN metal-insulator-semiconductor ultraviolet photodetectors using gallium oxide as gate layer. <i>Optics Express</i> , 2011 , 19, 12658-63	3.3	34
176	Enhanced output power of GaN-based LEDs with embedded AlGaN pyramidal shells. <i>Optics Express</i> , 2011 , 19, 12719-26	3.3	7
175	Investigation of the Carrier Dynamic in GaN-Based Cascade Green Light-Emitting Diodes Using the Very Fast Electrical-Optical Pump-Probe Technique. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 495-500	2.9	12
174	The Influence of a Piezoelectric Field on the Dynamic Performance of GaN-Based Green Light-Emitting Diodes With an InGaN Insertion Layer. <i>IEEE Electron Device Letters</i> , 2011 , 32, 656-658	4.4	3
173	Investigation of the Efficiency-Droop Mechanism in Vertical Red Light-Emitting Diodes Using a Dynamic Measurement Technique. <i>IEEE Photonics Technology Letters</i> , 2011 , 23, 1585-1587	2.2	8
172	GaN-Based Light-Emitting Diodes With Air Gap Array and Patterned Sapphire Substrate. <i>IEEE Photonics Technology Letters</i> , 2011 , 23, 1207-1209	2.2	2
171	Femtosecond ultrasonic spectroscopy using a piezoelectric nanolayer: Hypersound attenuation in vitreous silica films. <i>Applied Physics Letters</i> , 2011 , 99, 051913	3.4	17
170	Improved Power Conversion Efficiency of InGaN Photovoltaic Devices Grown on Patterned Sapphire Substrates. <i>IEEE Electron Device Letters</i> , 2011 , 32, 536-538	4.4	4
169	Influence of modulated fields on the Landau level properties of graphene. <i>Physical Review B</i> , 2011 , 83,	3.3	11
168	Enhanced Light Output of GaN-Based Light-Emitting Diodes With Embedded Voids Formed on Si-Implanted GaN Layers. <i>IEEE Electron Device Letters</i> , 2011 , 32, 1400-1402	4.4	9
167	Optical and Electrical Properties of μ -Slice InGaN/GaN Light Emitting Diodes Shaped by Focused Ion Beam Process. <i>Applied Physics Express</i> , 2011 , 4, 032104	2.4	2
166	AlGaInP/GaP Heterostructures Bonded with Si Substrate to Serve as Solar Cells and Light Emitting Diodes. <i>Journal of the Electrochemical Society</i> , 2010 , 157, H452	3.9	6
165	Improved Hydrogen Gas Generation Rate of n-GaN Photoelectrode with SiO ₂ Protection Layer on the Ohmic Contacts from the Electrolyte. <i>Journal of the Electrochemical Society</i> , 2010 , 157, B2668-9	2.9	11
164	Erbium-Doped All-Fiber Green Up-Conversion Amplified Emission in Silica-Based Fiber System. <i>Japanese Journal of Applied Physics</i> , 2010 , 49, 032701	1.4	
163	Polarized edge emission from GaN-based light-emitting diodes sandwiched by dielectric/metal hybrid reflectors. <i>Journal of Applied Physics</i> , 2010 , 108, 113102	2.5	2
162	Inverted Al _{0.25} Ga _{0.75} N/GaN ultraviolet p-i-n photodiodes formed on p-GaN template layer grown by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , 2010 , 97, 013502	3.4	23
161	Femtosecond laser-ultrasonic investigation of plasmonic fields on the metal/gallium nitride interface. <i>Applied Physics Letters</i> , 2010 , 97, 201102	3.4	9

160	AlGaIn-based ultraviolet photodetector with micropillar structures. <i>Applied Physics Letters</i> , 2010 , 96, 102104	3.4	5
159	GaN-based light emitting diodes with embedded SiO ₂ pillars and air gap array structures. <i>Applied Physics Letters</i> , 2010 , 97, 081103	3.4	27
158	Enhancement of the conversion efficiency of GaN-based photovoltaic devices with AlGaIn/InGaIn absorption layers. <i>Applied Physics Letters</i> , 2010 , 97, 021113	3.4	23
157	Ga-Doped ZnO/GaN Schottky Barrier UV Band-Pass Photodetector with a Low-Temperature-Grown GaN Cap Layer. <i>Japanese Journal of Applied Physics</i> , 2010 , 49, 04DF12	1.4	1
156	Effect of Thermal Annealing on the GaN Metal-Oxide-Semiconductor Capacitors with Gallium Oxide Gate Layer. <i>Journal of the Electrochemical Society</i> , 2010 , 157, H1019	3.9	9
155	InGaIn gallium nitride light-emitting diodes with reflective electrode pads and textured gallium-doped ZnO contact layer. <i>Applied Physics Letters</i> , 2010 , 96, 133504	3.4	21
154	Very-High Temperature (200 °C) and High-Speed Operation of Cascade GaN-Based Green Light-Emitting Diodes With an InGaIn Insertion Layer. <i>IEEE Photonics Technology Letters</i> , 2010 , 22, 1033-1035	2.3	9
153	Characterization of n-GaN with Naturally Textured Surface for Photoelectrochemical Hydrogen Generation. <i>Journal of the Electrochemical Society</i> , 2010 , 157, H1106	3.9	5
152	InGaIn light-emitting diodes with oblique sidewall facets formed by selective growth on SiO ₂ patterned GaN film. <i>Optics Express</i> , 2010 , 18 Suppl 4, A562-7	3.3	6
151	A Numerical Study of Thermal and Electrical Effects in a Vertical LED Chip. <i>Journal of the Electrochemical Society</i> , 2010 , 157, H31	3.9	21
150	GaN-Based LEDs With AZO:Y Upper Contact. <i>IEEE Transactions on Electron Devices</i> , 2010 , 57, 134-139	2.9	17
149	III-Nitride-Based Light-Emitting Diodes With GaN Micropillars Around Mesa and Patterned Substrate. <i>IEEE Transactions on Electron Devices</i> , 2010 , 57, 140-144	2.9	4
148	Sub-Bandgap Laser Light-Induced Excess Carrier Transport Between Surface States and Two-Dimensional Electron Gas Channel in AlGaIn/GaN Structure. <i>IEEE Journal of Quantum Electronics</i> , 2010 , 46, 112-115	2	4
147	Improved Performance of GaN-Based Blue LEDs With the InGaIn Insertion Layer Between the MQW Active Layer and the n-GaN Cladding Layer. <i>IEEE Journal of Quantum Electronics</i> , 2010 , 46, 513-517	2	30
146	GaN-Based Light-Emitting Diodes With Pillar Structures Around the Mesa Region. <i>IEEE Journal of Quantum Electronics</i> , 2010 , 46, 1066-1071	2	8
145	Photodetectors formed by an indium tin oxide/zinc oxide/p-type gallium nitride heterojunction with high ultraviolet-to-visible rejection ratio. <i>Applied Physics Letters</i> , 2009 , 94, 013512	3.4	21
144	The Output Power Enhancements of GaN-Based Blue Light-Emitting Diodes with Highly Reflective Ag/Cr/Au Trilayer Omnidirectional Reflective Electrode Pads. <i>Japanese Journal of Applied Physics</i> , 2009 , 48, 102103	1.4	6
143	GaN-Based LED with Embedded Microlens-like Structure. <i>Journal of the Electrochemical Society</i> , 2009 , 156, H976	3.9	6

142	Characterization of Gallium-Doped Zinc Oxide Contact on n-Type Gallium Nitride Epitaxial Layers. <i>Journal of the Electrochemical Society</i> , 2009 , 156, H679	3.9	2
141	. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2009 , 15, 1275-1280	3.8	13
140	GaN-Based Power Flip-Chip LEDs With Cu Submount. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2009 , 15, 1287-1291	3.8	6
139	The Structure of GaN-Based Transverse Junction Blue LED Array for Uniform Distribution of Injected Current/Carriers. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2009 , 15, 1292-1297	3.8	9
138	Electrical-optical analysis of a GaN/sapphire LED chip by considering the resistivity of the current-spreading layer. <i>Optical Review</i> , 2009 , 16, 213-215	0.9	19
137	High-Brightness InGaN/GaN Power Flip-Chip LEDs. <i>Journal of Lightwave Technology</i> , 2009 , 27, 1985-1989	4	10
136	Improvement of the Efficiency of InGaN/GaN Quantum-Well Light-Emitting Diodes Grown With a Pulsed-Trimethylindium Flow Process. <i>IEEE Photonics Technology Letters</i> , 2009 , 21, 414-416	2.2	5
135	Light Output Improvement of Oxide-Textured InGaN-Based Light-Emitting Diodes by Bias-Assisted Photoelectrochemical Oxidation With Imprint Technique. <i>IEEE Photonics Technology Letters</i> , 2009 , 21, 718-720	2.2	4
134	GaN-Based LEDs With Mesh ITO p-Contact and Nanopillars. <i>IEEE Photonics Technology Letters</i> , 2009 , 21, 1293-1295	2.2	2
133	GaN-Based LEDs With GaN μ s-Pillars Around Mesa, Patterned Substrate, and Reflector Under Pads. <i>IEEE Photonics Technology Letters</i> , 2009 , 21, 1659-1661	2.2	1
132	Demonstration of GaN-Based Solar Cells With GaN/InGaN Superlattice Absorption Layers. <i>IEEE Electron Device Letters</i> , 2009 , 30, 225-227	4.4	59
131	Improved Light Extraction Efficiency in AlGaInP Light-Emitting Diodes by Applying a Periodic Texture on the Surface. <i>IEEE Photonics Technology Letters</i> , 2008 , 20, 1724-1726	2.2	10
130	Linear Cascade GaN-Based Green Light-Emitting Diodes With Invariant High-Speed/Power Performance Under High-Temperature Operation. <i>IEEE Photonics Technology Letters</i> , 2008 , 20, 1896-1898	2.2	11
129	Phosphor-Free GaN-Based Transverse Junction White-Light Light-Emitting Diodes With Regrown n-Type Regions. <i>IEEE Photonics Technology Letters</i> , 2008 , 20, 449-451	2.2	12
128	Effect of Thickness of the p-AlGaIn Electron Blocking Layer on the Improvement of ESD Characteristics in GaN-Based LEDs. <i>IEEE Photonics Technology Letters</i> , 2008 , 20, 1142-1144	2.2	33
127	Ga-Doped ZnO Transparent Conductive Oxide Films Applied to GaN-Based Light-Emitting Diodes for Improving Light Extraction Efficiency. <i>IEEE Journal of Quantum Electronics</i> , 2008 , 44, 1211-1218	2	31
126	High-Speed GaN-Based Green Light-Emitting Diodes With Partially n-Doped Active Layers and Current-Confined Apertures. <i>IEEE Electron Device Letters</i> , 2008 , 29, 158-160	4.4	47
125	Focused Ion Beam Milled InGaIn/GaN Multiple Quantum Well Nanopillars. <i>Japanese Journal of Applied Physics</i> , 2008 , 47, 3130-3133	1.4	3

124	Low Operation Voltage of Nitride-Based LEDs with Al-Doped ZnO Transparent Contact Layer. <i>Electrochemical and Solid-State Letters</i> , 2008 , 11, H269		24
123	Enhancement in output power of blue gallium nitride-based light-emitting diodes with omnidirectional metal reflector under electrode pads. <i>Applied Physics Letters</i> , 2008 , 93, 103507	3-4	37
122	Effect of the Electrode Pattern on Current Spreading and Driving Voltage in a GaN/Sapphire LED Chip. <i>Journal of the Electrochemical Society</i> , 2008 , 155, H836	3-9	24
121	Four-Wavelengths-Mixed White Light Emitting Diodes with Dual-Wavelength-Pumped Green and Red Phosphors. <i>Japanese Journal of Applied Physics</i> , 2008 , 47, 6317-6319	1-4	
120	Ultraviolet bandpass Al _{0.17} Ga _{0.83} N/GaN heterojunction phototransistors with high optical gain and high rejection ratio. <i>Applied Physics Letters</i> , 2008 , 92, 053506	3-4	21
119	Ultraviolet band-pass photodetectors formed by Ga-doped ZnO contacts to n-GaN. <i>Applied Physics Letters</i> , 2008 , 92, 113512	3-4	17
118	Non-lithographic nanopatterning of InGaN/GaN multiple quantum well nanopillars by focused ion beams. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 2186-2188		2
117	The CL emission observation of the InGaN/GaN MQWs V shaped pits with different superlattices underlayers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 1639-1641		6
116	Improved Reliability and ESD Characteristics of Flip-Chip GaN-Based LEDs With Internal Inverse-Parallel Protection Diodes. <i>IEEE Electron Device Letters</i> , 2007 , 28, 346-349	4-4	32
115	Linear Cascade Arrays of GaN-Based Green Light-Emitting Diodes for High-Speed and High-Power Performance. <i>IEEE Photonics Technology Letters</i> , 2007 , 19, 1368-1370	2-2	13
114	Effects of leakage current and Schottky-like ohmic contact on the characterization of Al _{0.17} Ga _{0.83} N/GaN HBTs. <i>Solid-State Electronics</i> , 2007 , 51, 1073-1078	1-7	5
113	AlGaN ultraviolet metal-semiconductor-metal photodetectors grown on Si substrates. <i>Sensors and Actuators A: Physical</i> , 2007 , 135, 502-506	3-9	16
112	Enhanced efficiency of GaN-based light-emitting diodes with periodic textured Ga-doped ZnO transparent contact layer. <i>Applied Physics Letters</i> , 2007 , 90, 263511	3-4	74
111	Temperature-dependent study of n-ZnO/p-GaN diodes. <i>Applied Physics Letters</i> , 2007 , 90, 132111	3-4	15
110	Hole escape processes detrimental to photoluminescence efficiency in a blue InGaN multiple-quantum-well diode under reverse bias conditions. <i>Applied Physics Letters</i> , 2007 , 90, 161109	3-4	2
109	Largely variable electroluminescence efficiency with current and temperature in a blue (In, Ga)N multiple-quantum-well diode. <i>Applied Physics Letters</i> , 2007 , 91, 073501	3-4	7
108	Nonalloyed Cr/Au-based Ohmic contacts to n-GaN. <i>Applied Physics Letters</i> , 2007 , 91, 182106	3-4	67
107	Effect of Thermal Annealing on Ga-Doped ZnO Films Prepared by Magnetron Sputtering. <i>Journal of the Electrochemical Society</i> , 2007 , 154, H521	3-9	55

106	Variations of Channel Conductance in AlGaIn/GaN Structure with Sub-Bandgap Laser Light and Above-Bandgap Illuminations. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, 3382-3384	1.4	4
105	Crack-Free High-Brightness InGaIn/GaN LEDs on Si(111) with Initial AlGaIn Buffer and Two LT-Al Interlayers. <i>Journal of the Electrochemical Society</i> , 2007 , 154, H191	3.9	8
104	GaN-Based Ultraviolet p-i-n Photodiodes with Buried p-Layer Structure Grown by MOVPE. <i>Journal of the Electrochemical Society</i> , 2007 , 154, H182	3.9	5
103	Nitride-based light emitting diodes with indium tin oxide electrode patterned by imprint lithography. <i>Applied Physics Letters</i> , 2007 , 91, 013504	3.4	60
102	Emission Mechanism of Mixed-Color InGaIn/GaN Multi-Quantum-Well Light-Emitting Diodes. <i>Japanese Journal of Applied Physics</i> , 2006 , 45, 2463-2466	1.4	31
101	Nitride-based flip-chip p-i-n photodiodes. <i>IEEE Transactions on Advanced Packaging</i> , 2006 , 29, 483-487		3
100	Electroluminescence efficiency of blue InGaIn/GaN quantum-well diodes with and without an n-InGaIn electron reservoir layer. <i>Journal of Applied Physics</i> , 2006 , 100, 113105	2.5	39
99	Ultraviolet band-pass Schottky barrier photodetectors formed by Al-doped ZnO contacts to n-GaN. <i>Applied Physics Letters</i> , 2006 , 88, 043506	3.4	27
98	InGaIn light-emitting diodes with naturally formed truncated micropylramids on top surface. <i>Applied Physics Letters</i> , 2006 , 88, 113505	3.4	39
97	Improved performance of planar GaN-based p-i-n photodetectors with Mg-implanted isolation ring. <i>Applied Physics Letters</i> , 2006 , 89, 183509	3.4	12
96	Schottky barrier heights of metal contacts to n-type gallium nitride with low-temperature-grown cap layer. <i>Applied Physics Letters</i> , 2006 , 88, 032103	3.4	39
95	Planar GaN p-i-n photodiodes with n ⁺ -conductive channel formed by Si implantation. <i>Applied Physics Letters</i> , 2006 , 88, 203508	3.4	8
94	AlGaIn/GaN Schottky-barrier UV-B bandpass photodetectors with ITO contacts and LT-GaN cap layers. <i>Semiconductor Science and Technology</i> , 2006 , 21, 1064-1068	1.8	12
93	Effects of Thermal Annealing on Al-Doped ZnO Films Deposited on p-Type Gallium Nitride. <i>Journal of the Electrochemical Society</i> , 2006 , 153, G296	3.9	23
92	. <i>IEEE Sensors Journal</i> , 2006 , 6, 406-411	4	27
91	Flip-Chip p(GaN)-i(GaN)-n(AlGaIn) Narrowband UV-A Photosensors. <i>IEEE Sensors Journal</i> , 2006 , 6, 964-969		5
90	Nitride-based photodiode at 510-nm wavelength for plastic optical fiber communication. <i>IEEE Photonics Technology Letters</i> , 2006 , 18, 283-285	2.2	5
89	Enhanced light output of GaN-based power LEDs with transparent Al-doped ZnO current spreading layer. <i>IEEE Photonics Technology Letters</i> , 2006 , 18, 274-276	2.2	67

88	High efficiency and improved ESD characteristics of GaN-based LEDs with naturally textured surface grown by MOCVD. <i>IEEE Photonics Technology Letters</i> , 2006 , 18, 1213-1215	2.2	60
87	The improvement in modulation speed of GaN-based Green light-emitting diode (LED) by use of n-type barrier doping for plastic optical fiber (POF) communication. <i>IEEE Photonics Technology Letters</i> , 2006 , 18, 1636-1638	2.2	28
86	Phosphor-Free GaN-Based Transverse Junction Light Emitting Diodes for the Generation of White Light. <i>IEEE Photonics Technology Letters</i> , 2006 , 18, 2593-2595	2.2	13
85	Highly Reliable Nitride-Based LEDs With Internal ESD Protection Diodes. <i>IEEE Transactions on Device and Materials Reliability</i> , 2006 , 6, 442-447	1.6	12
84	Planar Ultraviolet Photodetectors Formed by Si Implantation into p-GaN. <i>Journal of the Electrochemical Society</i> , 2006 , 153, G799	3.9	3
83	Effect of low-temperature-grown GaN cap layer on reduced leakage current of GaN Schottky diodes. <i>Applied Physics Letters</i> , 2005 , 86, 052103	3.4	49
82	Comparison of low-temperature GaN, SiO ₂ , and SiN _x as gate insulators on AlGaIn/GaN heterostructure field-effect transistors. <i>Journal of Applied Physics</i> , 2005 , 98, 064506	2.5	16
81	Enhancement in light output of InGaN-based microhole array light-emitting diodes. <i>IEEE Photonics Technology Letters</i> , 2005 , 17, 1163-1165	2.2	43
80	Enhanced output power in GaN-based LEDs with naturally textured surface grown by MOCVD. <i>IEEE Electron Device Letters</i> , 2005 , 26, 464-466	4.4	48
79	AlGaIn-GaN Schottky-barrier photodetectors with LT GaN cap layers. <i>Journal of Crystal Growth</i> , 2005 , 283, 68-71	1.6	9
78	ICP etching of sapphire substrates. <i>Optical Materials</i> , 2005 , 27, 1171-1174	3.3	49
77	Fabrication and Characterization of In _{0.25} Ga _{0.75} N/GaN Multiple Quantum Wells Embedded in Nanorods. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, 7723-7725	1.4	3
76	Photoluminescence from In _{0.3} Ga _{0.7} N/GaN multiple-quantum-well nanorods. <i>Nanotechnology</i> , 2005 , 16, 448-450	3.4	6
75	Effect of Cl ₂ /Ar dry etching on p-GaN with Ni/Au metallization characterization. <i>Applied Physics Letters</i> , 2005 , 87, 252107	3.4	14
74	Aluminum gallium nitride ultraviolet photodiodes with buried p-layer structure. <i>Applied Physics Letters</i> , 2005 , 87, 043501	3.4	4
73	Effects of Thermal Annealing on Si-Implanted GaN Films Grown at Low Temperature by Metallorganic Vapor Phase. <i>Journal of the Electrochemical Society</i> , 2005 , 152, G813	3.9	3
72	Gratings in GaN Membranes. <i>Japanese Journal of Applied Physics</i> , 2004 , 43, 5854-5856	1.4	4
71	Si diffusion in p-GaN. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2004 , 22, 1727		13

70	Effect of GaN cap layer grown at a low temperature on electrical characteristics of Al _{0.25} Ga _{0.75} N/GaN heterojunction field-effect transistors. <i>Applied Physics Letters</i> , 2004 , 85, 1430-1432	3.4	8
69	Nitride-based LEDs with modulation-doped Al/sub 0.12/Ga/sub 0.88/N-GaN superlattice structures. <i>IEEE Transactions on Electron Devices</i> , 2004 , 51, 1743-1746	2.9	33
68	Nitride-based near-ultraviolet LEDs with an ITO transparent contact. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2004 , 106, 69-72	3.1	49
67	Lateral epitaxial patterned sapphire InGaN/GaN MQW LEDs. <i>Journal of Crystal Growth</i> , 2004 , 261, 466-470	3.6	63
66	Reduction of dark current in AlGaIn-GaN Schottky-barrier photodetectors with a low-temperature-grown GaN cap layer. <i>IEEE Electron Device Letters</i> , 2004 , 25, 593-595	4.4	35
65	Nitride-based LEDs with an SPS tunneling contact Layer and an ITO transparent contact. <i>IEEE Photonics Technology Letters</i> , 2004 , 16, 1002-1004	2.2	67
64	Nitride-based LEDs with 800/spl deg/C grown p-AlInGaIn-GaN double-cap layers. <i>IEEE Photonics Technology Letters</i> , 2004 , 16, 1447-1449	2.2	90
63	Experimental study of perpendicular transport in weakly coupled Al _x Ga _{1-x} N/GaN superlattices. <i>Applied Physics Letters</i> , 2003 , 83, 4975-4977	3.4	17
62	n-UV+Blue/Green/Red White Light Emitting Diode Lamps. <i>Japanese Journal of Applied Physics</i> , 2003 , 42, 2284-2287	1.4	84
61	GaN light-emitting diodes with omnidirectional reflectors	2003, 4996, 139	9
60	Electrical-efficiency analysis of GaN-based light-emitting diodes with interdigitated-mesa geometry. <i>Journal of Electronic Materials</i> , 2003 , 32, 312-315	1.9	
59	Gallium Nitride Diffractive Microlenses Using in Ultraviolet Micro-Optics System. <i>Optical Review</i> , 2003 , 10, 287-289	0.9	3
58	Si and Zn co-doped InGaIn-GaN white light-emitting diodes. <i>IEEE Transactions on Electron Devices</i> , 2003 , 50, 519-521	2.9	26
57	Nitride-based light emitting diodes with Si-doped In/sub 0.23/Ga/sub 0.77/N/GaN short period superlattice tunneling contact layer. <i>IEEE Transactions on Electron Devices</i> , 2003 , 50, 535-537	2.9	8
56	Nitride-based green light-emitting diodes with high temperature GaN barrier layers. <i>IEEE Transactions on Electron Devices</i> , 2003 , 50, 1766-1770	2.9	23
55	High brightness InGaIn green LEDs with an ITO on n/sup +/-SPS upper contact. <i>IEEE Transactions on Electron Devices</i> , 2003 , 50, 2208-2212	2.9	27
54	GaN diffractive microlenses fabricated with gray-level mask. <i>Optics Communications</i> , 2003 , 215, 75-78	2	10
53	Visible-blind GaN p-i-n photodiodes with an Al _{0.12} Ga _{0.88} N/GaN superlattice structure. <i>Solid-State Electronics</i> , 2003 , 47, 873-878	1.7	18

52	Nitride-based blue LEDs with GaN/SiN double buffer layers. <i>Solid-State Electronics</i> , 2003 , 47, 2019-2022	1.7	21
51	In _{0.23} Ga _{0.77} N/GaN MQW LEDs with a low temperature GaN cap layer. <i>Solid-State Electronics</i> , 2003 , 47, 2027-2030	1.7	52
50	MOCVD growth of InGaN/GaN blue light emitting diodes on patterned sapphire substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 2253-2256		4
49	High brightness InGaN/GaN LEDs with indium-tin-oxide as p-electrode. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 2227-2231		5
48	White-light emission from near UV InGaN-GaN LED chip precoated with blue/green/red phosphors. <i>IEEE Photonics Technology Letters</i> , 2003 , 15, 18-20	2.2	546
47	Improvement of near-ultraviolet InGaN-GaN light-emitting diodes through higher pressure grown underlying GaN layers. <i>IEEE Photonics Technology Letters</i> , 2003 , 15, 1050-1052	2.2	6
46	Improvement of near-ultraviolet InGaN-GaN light-emitting diodes with an AlGaIn electron-blocking layer grown at low temperature. <i>IEEE Photonics Technology Letters</i> , 2003 , 15, 1342-1344	2.2	32
45	Improved ESD protection by combining InGaN-GaN MQW LEDs with GaN Schottky diodes. <i>IEEE Electron Device Letters</i> , 2003 , 24, 129-131	4.4	56
44	Improvement of InGaN/GaN laser diodes by using a Si-doped In _{0.23} Ga _{0.77} N/GaN short-period superlattice tunneling contact layer. <i>IEEE Electron Device Letters</i> , 2003 , 24, 206-208	4.4	12
43	Characterization of GaN Schottky barrier photodetectors with a low-temperature GaN cap layer. <i>Journal of Applied Physics</i> , 2003 , 94, 1753-1757	2.5	35
42	Deep level defect in Si-implanted GaN n+p junction. <i>Applied Physics Letters</i> , 2003 , 82, 3671-3673	3.4	17
41	GaN metal-semiconductor-metal photodetectors with low-temperature-GaN cap layers and ITO metal contacts. <i>IEEE Electron Device Letters</i> , 2003 , 24, 212-214	4.4	84
40	GaN Schottky barrier photodetectors with a low-temperature GaN cap layer. <i>Applied Physics Letters</i> , 2003 , 82, 2913-2915	3.4	42
39	Carrier dynamics in nitride-based light-emitting p-n junction diodes with two active regions emitting at different wavelengths. <i>Journal of Applied Physics</i> , 2003 , 94, 2167-2172	2.5	48
38	400-nm InGaN-GaN and InGaN-AlGaIn multiquantum well light-emitting diodes. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2002 , 8, 744-748	3.8	196
37	Characterization of Si implants in p-type GaN. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2002 , 8, 767-772	3.8	34
36	High-efficiency InGaN-GaN MQW green light-emitting diodes with CART and DBR structures. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2002 , 8, 284-288	3.8	56
35	InGaN/GaN tunnel-injection blue light-emitting diodes. <i>IEEE Transactions on Electron Devices</i> , 2002 , 49, 1093-1095	2.9	48

34	Novel type of ohmic contacts to p-doped GaN using polarization fields in thin In _x Ga _{1-x} N capping layers. <i>Journal of Electronic Materials</i> , 2002 , 31, 416-420	1.9	4
33	Dependence of optical gain on direction of optically pumped cavity on (0001)-plane for InGaN/GaN multiple quantum well structure. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2002 , 93, 28-30	3.1	2
32	Observation of dislocation etch pits in epitaxial lateral overgrowth GaN by wet etching. <i>Solid-State Electronics</i> , 2002 , 46, 555-558	1.7	20
31	GaN p \bar{n} junction diode formed by Si ion implantation into p-GaN. <i>Solid-State Electronics</i> , 2002 , 46, 2179-2183	1.8	20
30	Piezoelectric effect on Al _{0.35} In _{0.65} N/GaN heterostructures. <i>Applied Physics Letters</i> , 2002 , 80, 2684-2686	3.4	6
29	Planar GaN n \bar{p} photodetectors formed by Si implantation into p-GaN. <i>Applied Physics Letters</i> , 2002 , 81, 4263-4265	3.4	37
28	High brightness green light emitting diodes with charge asymmetric resonance tunneling structure. <i>IEEE Electron Device Letters</i> , 2002 , 23, 130-132	4.4	49
27	Ohmic contacts to p-type GaN mediated by polarization fields in thin In _x Ga _{1-x} N capping layers. <i>Applied Physics Letters</i> , 2002 , 80, 986-988	3.4	57
26	n $\bar{+}$ -GaN formed by Si implantation into p-GaN. <i>Journal of Applied Physics</i> , 2002 , 91, 1845-1848	2.5	49
25	White-light emission from InGaN-GaN multiquantum-well light-emitting diodes with Si and Zn codoped active well layer. <i>IEEE Photonics Technology Letters</i> , 2002 , 14, 450-452	2.2	73
24	Nitride-based cascade near white light-emitting diodes. <i>IEEE Photonics Technology Letters</i> , 2002 , 14, 908-910	2.1	69
23	InGaN/GaN light emitting diodes activated in O/sub 2/ ambient. <i>IEEE Electron Device Letters</i> , 2002 , 23, 240-242	4.4	53
22	The doping process and dopant characteristics of GaN. <i>Journal of Physics Condensed Matter</i> , 2002 , 14, R657-R702	1.8	78
21	GaN metal-semiconductor-metal ultraviolet sensors with various contact electrodes. <i>IEEE Sensors Journal</i> , 2002 , 2, 366-371	4	91
20	Influence of Si-doping on the characteristics of InGaN-GaN multiple quantum-well blue light emitting diodes. <i>IEEE Journal of Quantum Electronics</i> , 2002 , 38, 446-450	2	135
19	Characterization of the properties of Mg-doped Al _{0.15} Ga _{0.85} N/GaN superlattices. <i>Solid-State Electronics</i> , 2001 , 45, 1665-1671	1.7	3
18	Characterization of p-type In _x Ga _{1-x} N grown by metalorganic chemical vapor deposition. <i>Solid-State Electronics</i> , 2001 , 45, 427-430	1.7	10
17	Low-resistance Ni/Au ohmic contact to Mg-doped of Al _{0.15} Ga _{0.85} N/GaN superlattices. <i>Solid-State Electronics</i> , 2001 , 45, 717-720	1.7	14

16	Polymer PBT/n-GaN metal-insulator-semiconductor structure. <i>Applied Physics Letters</i> , 2001 , 79, 4589-4593	3.4	17
15	InGaN-AlInGaN multi-quantum-well LEDs. <i>IEEE Photonics Technology Letters</i> , 2001 , 13, 559-561	2.2	96
14	GaN metal-semiconductor-metal ultraviolet photodetectors with transparent indium-tin-oxide Schottky contacts. <i>IEEE Photonics Technology Letters</i> , 2001 , 13, 848-850	2.2	131
13	Enhanced output power in an InGaN-GaN multi-quantum-well light-emitting diode with an InGaN current-spreading layer. <i>IEEE Photonics Technology Letters</i> , 2001 , 13, 1164-1166	2.2	34
12	Low-operation voltage of InGaN/GaN light-emitting diodes by using a Mg-doped Al/sub 0.15/Ga/sub 0.85/N/GaN superlattice. <i>IEEE Electron Device Letters</i> , 2001 , 22, 160-162	4.4	42
11	Crystal orientation dependence of optical gain in InGaN/GaN multiple-quantum-well structures. <i>Applied Physics Letters</i> , 2001 , 79, 1477-1479	3.4	7
10	Low-operation voltage of InGaN-GaN light-emitting diodes with Si-doped In/sub 0.3/Ga/sub 0.7/N/GaN short-period superlattice tunneling contact layer. <i>IEEE Electron Device Letters</i> , 2001 , 22, 460-462	4.4	118
9	Luminescence of an InGaN/GaN multiple quantum well light-emitting diode. <i>Solid-State Electronics</i> , 2000 , 44, 1055-1058	1.7	28
8	Investigation of the mechanism for Ti/Al ohmic contact on etched n-GaN surfaces. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2000 , 18, 729		38
7	Indium tin oxide ohmic contact to highly doped n-GaN. <i>Solid-State Electronics</i> , 1999 , 43, 2081-2084	1.7	33
6	Electrical derivative characteristics of ion-implanted AlGaInP/GaInP multi-quantum well lasers. <i>Solid-State Electronics</i> , 1998 , 42, 1867-1869	1.7	8
5	Effects of thermal annealing on the indium tin oxide Schottky contacts of n-GaN. <i>Applied Physics Letters</i> , 1998 , 72, 3317-3319	3.4	140
4	AlGaInP/GaP Light-Emitting Diodes Fabricated by Wafer Direct Bonding Technology. <i>Japanese Journal of Applied Physics</i> , 1996 , 35, 4199-4202	1.4	10
3	400nm InGaN/GaN and InGaN/AlGaIn multi-quantum well light-emitting diodes		2
2	Improved ESD reliability by using a modulation doped Al/sub 0.12/Ga/sub 0.88/N/GaN superlattice in nitride-based LED		1
1	Sea-Urchin-Like Bi ₂ S ₃ Microstructures Decorated with Graphitic Carbon Nitride Nanosheets for Use in Food Preservation. <i>ACS Applied Nano Materials</i> ,	5.6	3